PCN Number: 201		190329002.1		PCN	Date:	April 2, 2019			
Title:Qualification of Al Datasheet update				as an additiona	al Fab Site o	ption fo	or sel	ect CMOS	9T devices and
Customer Contact:		PCN Manager Der		Dept:	Dept: Q		ity Services		
Proposed 1 st Ship Date:		:	July 2, 2019 Estimated Samp Availability:		le	e Date provided at sample request.			
Change Type:									
Assembly Site				Assembly Process			Assembly Materials		
Desigi	n		Electrical Specification				Mechanical Specification		
Test Site				Packing/Shipping/Labeling			Test Process		
Wafer	Wafer Bump Site Wafer Bump Material			Wafer Bump Process		Sump Process			
🛛 Wafer	Wafer Fab Site 📃 Wafer Fab Materials				Wafer F	ab Process			
	Part number change								
PCN Details									

Description of Change:

Texas Instruments is pleased to announce the qualification of its AIZU fabrication facility as an additional Wafer Fab source for the selected devices listed in "Product Affected" section.

	Current Sites		Additional Sites			
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	
MAINEFAB	CMOS9T	200mm	AIZU	CMOS9T	200mm	

In addition, the datasheet number will be changing.

Device Family	Change From:	Change To:	
LP8556	SNVS871J	SNVS871K	

The LP8556 product datasheet is updated as seen in the change revision history below:



LP8556

Page

SNVS871K-JULY 2012-REVISED MARCH 2019

LP8556 High-efficiency LED backlight driver for tablets

4 Revision History

Changes from Revision J (January 2018) to Revision K

Added separate ESD Rating for the WQFN package - changed from "±2000" to "±1000"......6

These changes may be viewed at: http://www.ti.com/lit/ds/symlink/lp8556.pdf

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative): None

Changes to product identification resulting from this PCN:

Current			
Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City
MAINEFAB	CUA	USA	South Portland

New Fab Site

LP8556SQ-E08/NOPB

LP8556SQ-E09/NOPB

Chip Site	Chip Site Origin (20L)	Chip Site Country Code (21L)	Chip Site City
AIZU	CU2	JPN	Aizuwakamatsu-shi

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS G4 2DC: 2Q: MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 03/29/04 OPT: 39 LBL: 5A (L)T0:1750 Product Affected Group:		(1P) SN74LS07NSR (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY (1T) 7523483S12 (P) (2P) REV: (20L) CS0: SHE (21L) CC0:USA (21L) AS0: MLA (23L) ACO: MYS			
Product Affected Group:					
LP8556SQ-E00/NOPB	LP8556SQE-E00/NOPB	LP8556SQE-E09/NOPB LP8556SQX-E08/NOPB			

LP8556SQX-E00/NOPB

Qualification Report

LP8556SQE-E08/NOPB

Approve Date 1-Feb-2019

Qualification Deputs

Qualification Results				
Data Displayed as: Number of lots /	Total sample size / Total failed			

Test Name / Condition	Duratian	Qual Device:				
	Duration	LP8556SQE0WZ85	QBS Product Reference: LP8556SQE	QBS Product/Process Reference: LP8556TMX-E09/S1	QBS Package Reference: LMH6517SQE/NOPB	QBS Package Reference: DS25CP102QSQ
toclave	96 Hours		-	-	1/50/0	2/154/0
ectrical Characterization	(Per Datasheet Parameters)	1/30/0	-	-	-	-
rly Life Failure Rate, 125C	48 Hours	-	-	3/913/0	-	3/1599/0
ased HAST, 130C/85%RH	96 Hours	-	-	2/154/0	-	-
ased HAST, 110C/85%RH	264 Hours	-	-	1/77/0	-	-
gh Temp. Storage Bake, 150C	1000 Hours	-	-	1/77/0	-	1/77/0
e Test, 125C	1000 Hours	-	-	3/228/0	-	2/153/0
mperature Cycle, -65/150C	500 Cycles	-	-	3/231/0	3/231/0	2/154/0
mp Humidity 85C/85%Rh	1000 Hours	-	-	-	-	2/154/0
Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	-	-
D - HBM	1000 V	1/3/0	1/3/0	1/3/0	-	-
D - HBM	2500 V	-	-	1/3/0	-	1/3/0
D - CDM	1000 V	-	-	1/3/0	-	1/3/0
D - CDM	1500 V	1/3/0	1/3/0	-	-	-
tch-up	(per JESD78)	1/12/0	1/12/0	3/36/0	-	1/6/0
nufacturability (Assembly)	(Per Mfg. Site Specification)	1/Pass	-	-	-	-
	trical Characterization Life Failure Rate, 126C ed HAST, 130C/85%RH ed HAST, 110C/85%RH Temp. Storage Bake, 150C Test, 125C perature Cycle, -65/150C p Humidity 85C/85%RH ased HAST, 130C/85%RH - HBM - HBM - CDM - COM - UP	Interference (Per Datasheet Parameters) Life Failure Rate, 125C 48 Hours ed HAST, 130C/85%RH 96 Hours ed HAST, 110C/85%RH 264 Hours ed HAST, 110C/85%RH 264 Hours remp. Storage Bake, 150C 1000 Hours perature Cycle, -65/150C 500 Cycles b Humidity 85C/85%Rh 1000 Hours sed HAST, 130C/85%RH 96 Hours - HBM 2600 V - CDM 1000 V - LQD (Per JESD78) ufacturability (Assembly) (Per Mfg. Site Specification)	trical Characterization (Per Datasheet Parameters) 1/30/0 Life Failure Rate, 125C 48 Hours - ed HAST, 130/085%RH 96 Hours - ed HAST, 100/085%RH 264 Hours - remp. Storage Bake, 150C 1000 Hours - rest, 125C 1000 Hours - perature Cycle, -65/150C 500 Cycles - prumidity 85C/85%Rh 1000 Hours - ased HAST, 130C/85%RH 96 Hours - -HBM 1000 V 1/3/0 -HBM 2500 V - -CDM 1000 V 1/3/0 -up (per JESD78) 1/12/0 ufacturability (Assembly) (Per Mfg. Site Specification) 1/Pass	trical Characterization (Per Datasheet Parameters) 1/30/0 - Life Failure Rate, 125C 48 Hours - - - ed HAST, 130C/85%RH 96 Hours - - - ed HAST, 100C/85%RH 264 Hours - - - remp. Storage Bake, 150C 1000 Hours - - - rest, 125C 1000 Hours - - - perature Cycle, -65/150C 500 Cycles - - - of Humidity 85C/85%Rh 1000 Hours - - - sed HAST, 130C/85%RH 96 Hours - - - - HBM 1000 V 1/3/0 1/3/0 - - HBM 2500 V - - - - CDM 1600 V 1/3/0 1/3/0 - - Lup (per JESD78) 1/12/0 1/12/0 ufacturability (Assembly) (Per Kig. Site Specification) 1/Pass -	Instruction (Per Datasheet Parameters) 1/30/0 - - Life Failure Rate, 125C 48 Hours - - 3/913/0 et HAST, 130C/85%RH 96 Hours - - 2/164/0 et HAST, 130C/85%RH 264 Hours - 1/77/0 Temp. Storage Dake, 150C 1000 Hours - - 1/77/0 Temp. Storage Dake, 150C 1000 Hours - - 3/228/0 perature Cycle, -65/150C 500 Cycles - - 3/231/0 o Humidity 85C/85%Rh 1000 Hours - - - - sed HAST, 130C/85%RH 1000 Hours - - - - - sed HAST, 130C/85%RH 1000 Hours - <t< td=""><td>Instruction (Per Datasheet Parameters) 1/30/0 - - - Life Failure Rate, 125C 48 Hours - - 3/913/0 -</td></t<>	Instruction (Per Datasheet Parameters) 1/30/0 - - - Life Failure Rate, 125C 48 Hours - - 3/913/0 -

- QBS; Qual By Similarity - Qual Device LP8565SQE0W285/NOPB is qualified at LEVEL1-260C - HBM Electrostatic Discharge Sensitivity in datashed shall be changed to new measured values

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours - The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours - The following are equivalent Temp Cycle options per JESD47-56C/125C/100 Cycles and -65C/150C/600 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/ Green/Pb-Free Status: Qualified Pb-Free(SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
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Asia Pacific	PCNAsiaContact@list.ti.com
WW PCN Team	PCN ww admin team@list.ti.com

LP8556SQX-E09/NOPB